Paola Alippi

List of Publications by Year
in descending order

65 papers	1,484 citations	361045 20 h-index	315357 38 g-index
65 all docs	65 docs citations	65 times ranked	2138 citing authors

#	Article	IF	Citations
1	Disclosing the Nature of Asymmetric Interface Magnetism in Co/Pt Multilayers. ACS Applied Materials & Interfaces, 2022, 14, 12766-12776.	4.0	8
2	A systematic study of the valence electronic structure of cyclo(Glyâ€“Phe), cyclo(Trpâ€“Tyr) and cyclo(Trpâ€“Trp) dipeptides in the gas phase. Physical Chemistry Chemical Physics, 2021, 23, 26793-26805.	1.3	4
3	Impact of the Substrate Work Function on Self-Assembling and Electronic Structure of Adsorbed Ruthenium Phthalocyanine. Journal of Physical Chemistry C, 2020, 124, 23295-23306.	1.5	4
4	The electronic structure of Îµ-Ga2O3. APL Materials, 2019, 7, .	2.2	49
5	Effects of cobalt substitution on ZnO surface reactivity and electronic structure. Journal of Materials Chemistry C, 2019, 7, 8364-8373.	2.7	13
6	A Ruâ€“Ru pair housed in ruthenium phthalocyanine: the role of a â€œcageâ€•architecture in the molecule coupling with the Ag(111) surface. Physical Chemistry Chemical Physics, 2017, 19, 1449-1457.	1.3	7
7	Unexpected Rotamerism at the Origin of a Chessboard Supramolecular Assembly of Ruthenium Phthalocyanine. Chemistry - A European Journal, 2017, 23, 16319-16327.	1.7	11
8	Ferromagnetism and Conductivity in Hydrogen Irradiated Co-Doped ZnO Thin Films. ACS Applied Materials & Interfaces, 2016, 8, 12925-12931.	4.0	25
9	Electronic structure of hydrogenated diamond: Microscopical insight into surface conductivity. Physical Review B, 2016, 94, .	1.1	8
10	The effect of Co doping on the conductive properties of ferromagnetic Zn_xCo_{1â^'x}O films. Journal of Materials Chemistry C, 2015, 3, 10188-10194.	2.7	17
11	Defect-induced magnetism in cobalt-doped ZnO epilayers. , 2014, , .		1
12	Multigap absorption inCaCu3Ti4O12and the prediction capability ofab initiomethods. Physical Review B, 2014, 90, .	1.1	2
13	Impurity-vacancy complexes and ferromagnetism in doped sesquioxides. Physical Review B, 2014, 89, .	1.1	9
14	Supramolecular and Chiral Effects at the Titanyl Phthalocyanine/Ag(100) Hybrid Interface. Journal of Physical Chemistry C, 2014, 118, 5255-5267.	1.5	20
15	Interfacial Engineering of P3HT/ZnO Hybrid Solar Cells Using Phthalocyanines: A Joint Theoretical and Experimental Investigation. Advanced Energy Materials, 2014, 4, 1301694.	10.2	42
16	Connections between local and macroscopic properties in solids: The case of N in III-V-N alloys. Physical Review B, 2014, 89, .	1.1	7
17	XAS, XES and DFT simulations to bridge local and macroscopic properties in GaAsN. Acta Crystallographica Section A: Foundations and Advances, 2014, 70, C1520-C1520.	0.0	0
18	Influence of the surface structure on the magnetic properties of Zn1â^'xCoxO. Applied Physics Letters, 2012, 101, 252101.	1.5	1

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19	A hybrid zinc phthalocyanine/zinc oxide system for photovoltaic devices: a DFT and TDDFPT theoretical investigation. Journal of Materials Chemistry, 2012, 22, 440-446.	6.7	32
20	Zinc Oxideâ€“Zinc Phthalocyanine Interface for Hybrid Solar Cells. Journal of Physical Chemistry C, 2012, 116, 15439-15448.	1.5	36
21	Magnetism and unusual Cu valency in quadruple perovskites. European Physical Journal B, 2012, 85, 1.	0.6	10
22	Clusters and Magnetic Anchoring Points in (Ga,Fe)N Condensed Magnetic Semiconductors. Physical Review Letters, 2011, 107, 196401.	2.9	23
23	Evidence of Cobalt-Vacancy Complexes in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Zn</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mi mathvariant="normal">O</mml:mi></mml:math>Dilute Magnetic Semiconductors. Physical Review Letters, 2011, 107, 127206.	2.9	86
24	How much room for BiGa heteroantisites in GaAs1â^’xBix?. Applied Physics Letters, 2011, 99, .	1.5	20
25	Bound states of the Fe impurity in wurtzite GaN from hybrid density-functional calculations. Physical Review B, 2011, 84, .	1.1	19
26	Magnetic and X-ray absorption investigations of Co-doped ZnO films. Journal of Physics: Conference Series, 2010, 200, 072025.	0.3	1
27	Native point defects in CaCu₃Ti₄O₁₂. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012015.	0.3	7
28	Reorientable dipolar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Cu</mml:mtext></mml:mrow><mml:mrow><mml:mtext>Ca</mml:m and anomalous screening in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>CaCu</mml:mtext></mml:mrow><mml:mn>3</mml:mn></mml:m Physical Review B, 2010, 81, .	1.1	11
29	Deep versus Shallow Behavior of Intrinsic Defects in Rutile and Anatase TiO₂ Polymorphs. Journal of Physical Chemistry C, 2010, 114, 21694-21704.	1.5	138
30	Oxygen vacancies and OH species in rutile and anatase TiO2 polymorphs. Catalysis Today, 2009, 144, 177-182.	2.2	67
31	Properties of hydrogen and hydrogenâ€“vacancy complexes in the rutile phase of titanium dioxide. Physical Review B, 2009, 80, .	1.1	60
32	Ab initiostudy of the electronic states induced by oxygen vacancies in rutile and anatase<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>TiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msu Physical Review B, 2008, 78, .	1.1	239
33	Temperature Dependent Reaction of Thin Ni-Silicide Transrotational Layers on [001]Si. , 2007, , .		1
34	Excimer Laser Annealing of Ion-Implanted Silicon: Dopant Activation, Diffusion and Defect Formation. , 2007, , .		0
35	The Site of In Dopants in Si. AIP Conference Proceedings, 2007, , .	0.3	0
36	Effects of interface bonding on the conductance of metalâ€“carbon nanotubeâ€“metal systems. Materials Science and Engineering C, 2007, 27, 1102-1107.	3.8	2

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37	Experimental determination of the local geometry around In and Inâ€“C complexes in Si. Applied Physics Letters, 2006, 88, 212102.	1.5	8
38	Structural characterization of Ni2Si pseudoepitaxial transrotational structures on [001] Si. Acta Crystallographica Section B: Structural Science, 2006, 62, 729-736.	1.8	14
39	Ultra-shallow junction by laser annealing: Integration issues and modelling. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 1-8.	0.6	2
40	The effect of thermal treatments on the local geometry around indium in In and In+C high dose implanted Si. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 59-62.	0.6	4
41	Electronic Structure of Bulk and Defected CaCu3Ti4O12. ECS Transactions, 2006, 3, 291-297.	0.3	5
42	Ab Initio Investigations of Textured Ni2Si Films on Silicon. ECS Transactions, 2006, 3, 149-155.	0.3	1
43	Role of light scattering in excimer laser annealing of Si. Applied Physics Letters, 2005, 86, 161905.	1.5	21
44	Material modifications induced by laser annealing in two-dimensional structures. Applied Physics Letters, 2004, 84, 4738-4740.	1.5	22
45	Neutral boron-interstitial clusters in crystalline silicon. Physical Review B, 2004, 69, .	1.1	19
46	A phase-field approach to the simulation of the excimer laser annealing process in Si. Journal of Applied Physics, 2004, 95, 4806-4814.	1.1	69
47	Indium in silicon: interactions with native defects and with C impurities. Materials Research Society Symposia Proceedings, 2004, 810, 311.	0.1	0
48	Role of C and Ge in the electrical activation of In implanted in Silicon. Materials Research Society Symposia Proceedings, 2004, 810, 404.	0.1	0
49	Technology Computer Aided Design of Ultra-shallow Junctions in Si Devices Formed by Laser Annealing Processes. Materials Research Society Symposia Proceedings, 2004, 810, 269.	0.1	4
50	Computational methods for the simulation of the excimer laser annealing in MOS technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 100-104.	1.7	0
51	Energetics and diffusivity of indium-related defects in silicon. Physical Review B, 2004, 69, .	1.1	20
52	Electrical activation phenomena induced by excimer laser annealingin B-implanted silicon. Applied Physics Letters, 2004, 85, 2268-2270.	1.5	11
53	Atomic scale computer aided design for novel semiconductor devices. Computational Materials Science, 2003, 27, 10-15.	1.4	6
54	Role of the indiumâ€“carbon interaction on In diffusion and activation in Si. Applied Physics Letters, 2003, 83, 1956-1958.	1.5	12

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55	Atomistic Study of Boron Clustering in Silicon. Solid State Phenomena, 2002, 82-84, 163-170.	0.3	0
56	Atomic-scale characterization of boron diffusion in silicon. Physical Review B, 2001, 64, .	1.1	43
57	Energetics and diffusivity of atomic boron in silicon by density-functional-based tight-binding simulations. Computational Materials Science, 2001, 22, 44-48.	1.4	10
58	A multi-scale atomistic study of the interstitials agglomeration in crystalline Si. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 154-159.	0.6	7
59	From Point to Extended Defects in Silicon: A Theoretical Study. Solid State Phenomena, 2001, 85-86, 177-202.	0.3	2
60	Triple junctions and elastic stability of polycrystalline silicon. Physical Review B, 2000, 63, .	1.1	17
61	Lattice-strain field induced by{311}self-interstitial defects in silicon. Physical Review B, 2000, 62, 1815-1820.	1.1	27
62	Tetragonal states from epitaxial strain on metal films. Physical Review B, 1998, 57, 1971-1975.	1.1	45
63	Understanding Structure and Electronic Properties of Extended Self-Interstitial Defects in Silicon. Materials Research Society Symposia Proceedings, 1998, 538, 353.	0.1	0
64	Alkali-metal plasmons, pseudopotentials, and optical sum rules. Physical Review B, 1997, 55, 13835-13841.	1.1	6
65	Strained Tetragonal States and Bain Paths in Metals. Physical Review Letters, 1997, 78, 3892-3895.	2.9	129